

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	132	trench adj element adj isolation adj region	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/10/19 12:43
S2	88	S1 and @pd<"20030101"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/10/18 13:07
S5	5210	(257/93,374,446,501,504,506,509, 725,62,336,408,519,549,261).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2005/10/18 14:53
S6	10	S5 and trench adj element adj isolation adj region	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/10/18 13:07
S7	6	S6 and @pd<"20030101"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/10/18 13:07
S8	5210	(257/93,374,446,501,504,506,509, 725,62,336,408,519,549,261).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2005/10/18 14:53
S9	1077	S8 and insulating adj layer	USPAT	OR	OFF	2005/10/18 14:54
S10	40	S9 and (HDP-CvD or (TEOS adj plasma adj CvD) or SOG)	USPAT	OR	OFF	2005/10/18 15:03
S11	14	S8 and (doped adj layers) with (conductivity)	USPAT	OR	OFF	2005/10/18 15:25
S12	1	S8 and (doped adj layers) with (memory adj cell)	USPAT	OR	OFF	2005/10/18 15:29
S13	3179	SRAM with(memory adj cell)	USPAT	OR	OFF	2005/10/18 15:29
S14	3179	SRAM with (memory adj cell)	USPAT	OR	OFF	2005/10/18 15:30
S15	66	S14 and (doped adj layer)	USPAT	OR	OFF	2005/10/18 15:52
S16	11	S14 and (doped adj layer) same conductivity	USPAT	OR	OFF	2005/10/18 15:30
S17	11	("2" adj doped adj layer)	USPAT	OR	OFF	2005/10/18 15:34
S18	13	(("2" or two) adj doped adj layer)	USPAT	OR	OFF	2005/10/18 15:34
S19	1	("5955768").PN.	USPAT; USOCR	OR	OFF	2005/10/19 12:43